

**1. Scope :**

This specification applies to PN silicon photodiode chips,  
Device NO. PD-0340.

**2. Structure :**

- 2-1. Planar type : PN Diode.  
2-2. Electrodes :  
Top side (Anode ) : Aluminum alloy .  
Back side (Cathode ) : Gold alloy .

**3. Size :**

- 3-1. Chip size : 40 mils × 40 mils ( 1.016 mm × 1.016 mm ).  
3-2. Chip thickness :  $8.6 \pm 1.2$  mils (  $0.220 \pm 0.030$ mm ).  
3-3. Active area : 32 mils × 32 mils ( 0.813 mm × 0.813 mm ).  
3-4. Bonding pad ( Anode ) : 5.4 mils ( 0.137 mm ) Diameter.  
3-5. Pattern drawing : Refer to the attached drawing.

**4. Electro-optical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark current	$I_D$	$V_R=10V$ $E_e=0mW/cm^2$			10	nA
*Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	33			V
Open circuit voltage	$V_{oc}$	$T=2856K$ $E_e=5mW/cm^2$		440		mV
Short circuit Current	$I_{sc}$	$T=2856K$ $E_e=5mW/cm^2$		7		$\mu A$
Reverse light current	$I_L$	$V_R =5V$ $T=2856K$ $E_e=5mW/cm^2$		7		$\mu A$
Total Capacitance	$C_T$	$V_R =5V$ $E_e=0mW/cm^2$ $f=1MHz$		10		pF

\*Based on 100% probing

